BSIMSOIv4.4



BSIM Group

Tanvir Morshed, Darsen Lu, Yogesh Chauhan, Sriramkumar Venugopalan, Mohammed Karim, Ali Niknejad and Chenming Hu

> Dept. of Electrical Engineering and Computer Sciences, University of California, Berkeley

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BSIM SOI Bug Fixes and Enhancements

NF Scaling of Rds

```
file: b4soinoi.c line: 366
Issue: Bug in TNOI Model = 0
switch( model->B4SOItnoiMod )
case 0:
     NevalSrc(&noizDens[B4SOIIDNOIZ],
       &InNdens[B4SOIIDNOIZ], ckt,
       THERMNOISE,
       here->B4SOIdNodePrime,
       here->B4SOIsNodePrime,
       (here->B4SOIueff
       * FABS(here->B4SOIginv
             / (pParam->B4SOIleff
             * pParam->B4SOIleff
             + here->B4SOIueff*FABS
               (here->B4SOIqinv)
             * here->B4SOIrds)))
             * tempRatioSH
             * model->B4SOIntnoi );
```

here->B4SOIqinv is scaled by NF, while here->B4SOIrds is not

NF Scaling of Rds

Bug-fix: here->B4SOIrds is scaled by NF.

Previous code: File: b4soild.c line: 2820

here->B4SOIrds = Rds;

Modification:

here->B4SOIrds = Rds/here->B4SOInf;

Reported By: Lawrence Wagner, IBM

Negative 'rdsw' and 'rds0'

Negative 'rdsw' and 'rds0':

- The implementation of 'rdsw' and 'rds0' checks are different in C code and VA
- The VA code does not allow negative 'rdsw' and 'rds0' while
 C code does
- C code does the check in only PARAMCHK = 1, Verilog-A does in both
- QA test is done in PARAMCHK=0

Negative 'rdsw' and 'rds0'

Considerations:

- ADI and IBM expressed concern about allowing negative 'rdsw' and 'rds0'
- Last CMC meeting all agreed to implement the above features

Modification:

 According to CMC's recommendation the check is implemented irrespective of 'PARAMCHK'; C and VA codes behave identical

Vb blow up in SOIMOD=2

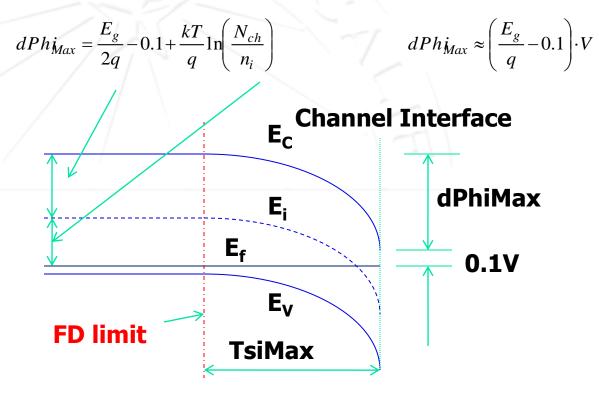
- b4soild.c line 2150:
- Vbs0 is evaluated as (BSIMSOIv 4.3 manual: Page 50)

$$V_{bs0} = \frac{C_{Si}}{C_{Si} + C_{BOX}} \cdot \left(phi - \frac{\left(qN_{ch}\left(1 + N_{LX}/L_{eff}\right)\right)}{2\varepsilon_{Si}} \cdot T_{Si}^{2}\right) + V_{nonideal} + \Delta V_{DIBL}\right) + \eta_{e} \frac{C_{BOX}}{C_{Si} + C_{BOX}} \cdot \left(V_{es} - V_{FBb}\right)$$
where $C_{Si} = \frac{\varepsilon_{Si}}{T_{Si}}$, $C_{BOX} = \frac{\varepsilon_{OX}}{T_{BOX}}$, $C_{OX} = \frac{\varepsilon_{OX}}{T_{OX}}$

- The highlighted term is Qsi/(2*Csi)
- High values of Nch / Tsi combination causes un-relistic
 Vbs values (-50V)

Check needed on Band Bending

Maximum allowed band bending and N_{ch}/T_{si} limit in SOIMOD=2:



Implemented Correction

• If
$$\frac{qN_{ch}\left(1+N_{LX}/L_{eff}\right)}{2\varepsilon_{Si}} \cdot T_{Si}^2$$
 exceeds dPhiMax in

SOIMOD=2, set Nch=NchMax, where:

$$N_{ch\text{max}} = \frac{dPh_{Max} \cdot 2\varepsilon_{Si}}{q \cdot T_{Si}^2 \cdot (1 + N_{lx}/L_{eff})}$$

- This check applies to SOIMOD=2 only.
- An warning is issued to the user.
- File: b4soiset.c (line:2173)

Enhancement of Fringe Capacitance

IBM's request for enhanced sidewall fringe capacitance formulation (CMC Action item 10Q3.13):

Current code:

csesw = csdesw*ln(1+Tsi/Tbox) (b4soitemp.c line: 1670)

IBM proposal: csesw = csdesw*ln[2*(1+Tsi/Tbox)]

Implemented: csesw = csdesw*In[Cfrcoeff*(1+Tsi/Tbox)]

Here Cfrcoeff (new model parameter) is given a default value = 1 for backward compatibility and a maximum limit of 2.

Temperature Derivative Fixes

 In SOIMOD=1 and 2, extensive derivative fixes are provided by Lawrence Wagner and Calvin Bittner. Please check the file 'BSIMSOIv4.4_Derivative_Fixes' for details.